Abstracts

Bias-dependent linear, scalable millimeter-wave FET model

J. Wood and D.E. Root. "Bias-dependent linear, scalable millimeter-wave FET model." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1381-1384.

This paper describes a measurement-based, bias-dependent, linear equivalent circuit FET/HEMT model that is accurate to at least 100 GHz and scalable up to 12 parallel gate fingers and from 100-1000 /spl mu/m total gate width. The equivalent circuit element values are determined at each bias point in V/sub gs/-V/sub ds/ space.

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